Toyota Technological Institute Graduate School of Engineering

Admission Guidelines for Students of National Chung Hsing University for Double Degree Program <For enrollment in April 2026>

1. Admission Capacity:

Four (4)

2. Fields of Research/Education:

- · Mechanical Systems Engineering
- · Electronics and Information Engineering
- · Materials Science and Engineering

Choose one from among the laboratories in the list attached.

3. Admission Requirements:

Applicants must be graduate students enrolled at a university with which the Double Degree Program has been established, and also must be recommended by the department chair of the home university.

4. English Skills:

Applicants are required to have a minimum of one of the followings: a TOEIC® L&R or L&R IP score of 550; a TOEFL iBT® score of 57; or a TOEFL ITP® score of 487 at the time of the application for admission. Applications must submit the original copy of the official score report.

5. Japanese Skills:

Applicants are expected to have Japanese skills enough to understand the courses. Classes and examinations are generally instructed in Japanese.

6. Application Procedure:

Applicants are required to submit the following documents (1)-(5):

(1) Application Form for Admission (form provided)

Prior to filling in the name of a laboratory which you hope to work in, contact the professor (who you wish to work with) and obtain the consent that you will put the laboratory name down in the application form.

※ Please check if the laboratory can accept Double Degree students or not. Some professors may not accept students in a given year.

(2) Certificate of Enrollment

Official transcripts with authorized signature or seal.

Please attach a Japanese or an English translation if the original documents are written in languages other than Japanese or English.

(3) Academic Records, Graduate and Undergraduate

Official transcripts with authorized signature or seal.

Please attach a Japanese or an English translation if the original documents are written in languages other than Japanese or English.

(4) Letter of Recommendation (form provided)

To be written by the department chair of the home university.

(5) TOEFL or TOEIC Score Record

The original copy of TOEFL Official Score Report or TOEIC Official Score report/Certificate.

* A student visa needs to be ready before you enroll in the institute

7. Submission of Application Documents:

Admissions Office

Toyota Technological Institute

2-12-1 Hisakata, Tempaku-ku

Nagoya, JAPAN 468-8511

Tel: +81-52-802-1111

Fax: +81-52-809-1721

8. Application Period:

All application documents must be sent via postal mail and reach TTI no later than Friday, November 28, 2025.

(We do not accept the documents sent by e-mail.)

9. Selection Procedures:

Applicants will be admitted based on the submitted documents.

10. Notification of Results:

Applicants will be notified of the results of acceptance as soon as the selection has been finished.

11. Date of enrollment:

New academic year starts in April.

*Please add @toyota-ti.ac.jp

| | Laboratories | Name | Position | E-mail * |
|--|----------------------------------|---------------------|--------------|---------------|
| Mechanical Systems Engineering | Elvid Evainassina | Tarou Handa | Prof. | handa |
| | Fluid Engineering | Yasumasa Watanabe | Assoc. Prof. | yswatanabe |
| | Computational Mechanics | Yoshinori Shiihara | Assoc. Prof. | shiihara |
| | Design Engineering | Masakazu Kobayashi | Assoc. Prof. | kobayashi |
| | Innovative Machine | Katsushi Furutani | Prof. | furutani |
| | Micro-Nano Mechatronics | Minoru Sasaki | Prof. | mnr-sasaki |
| | Wilcro-Nano Mechatronics | Deqing Kong | Assoc. Prof. | kong |
| Electronics and Information Engineering | Semiconductor | Yoshio Ohshita | Prof. | y_ohshita |
| | Functional Semiconductor Devices | Toshinori Numata | Prof. | numata |
| | runctional Semiconductor Devices | Sho Nakosai | Assoc. Prof. | nakosai |
| | Photovoltaic Devices | Nobuaki Kojima | Lecturer | nkojima |
| tronic | Laser Science | Takao Fuji | Prof. | fuji |
| cs ar | Laser Science | Tetsuhiro Kudo | Lecturer | kudo |
| าd In eerir | Spintronics | Kenji Tanabe | Assoc. Prof. | tanabe |
| form | Control System | Michihiro Kawanishi | Assoc. Prof. | kawa |
| ation | Information and Communications | Yojiro Mori | Prof. | mori |
| | Computational Intelligence | Yutaka Sasaki | Prof. | yutaka.sasaki |
| | Intelligent Information Media | Norimichi Ukita | Prof. | ukita |
| | Knowledge and Data Engineering | Makoto Miwa | Prof. | makoto-miwa |
| Materials Science and Engineering | Optical Functional Materials | Takenobu Suzuki | Assoc. Prof. | takenobu |
| | T M (: 1 | Tsunehiro Takeuchi | Prof. | t_takeuchi |
| | Energy Materials | Masaharu Matsunami | Assoc. Prof. | matunami |
| | Theoretical Physics | Tsunehide Kuroki | Prof. | kuroki |
| | Mathematical Physics | Shinya Tomizawa | Prof. | tomizawa |
| | Surface Science | Masamichi Yoshimura | Prof. | yoshi |
| | Surface Science | Masanori Hara | Assoc. Prof. | haram |
| | Polymer Chemistry | Kenta Kokado | Prof. | kokado |
| gr | Catalytic Organic Chemistry | Yukihiro Motoyama | Prof. | motoyama |

APPLICATION FORM

ADMISSION FOR STUDENTS OF NATIONAL CHUNG HSING UNIVERSITY

TOYOTA TECHNOLOGICAL INSTITUTE
GRADUATE SCHOOL OF ENGINEERING
DOUBLE DEGREE COURSE
<For enrollment in April 2026>

ダブルディグリー留学生入学志願書 豊田工業大学大学院工学研究科修士課程 <2026 年 4 月入学>

Instruction 記入上の注意

1. Application documents should be written either in Japanese or in Roman block letters.

記入は日本語またはローマ字ブロック体を用いてください。

- 2. Numbers should be in Arabic figures. 数字は算用数字を用いてください。
- 3. Years should be written in the Anno Domini system. 年号はすべて西暦としてください。
- 4. Proper nouns should be written in full, and not be abbreviated. 固有名詞はすべて正式な名称とし、一切省略しないでください。

Attach Photo Full Face (4cm×3cm) Taken within the past 3 months

顔写真添付のこと 3ヶ月以内の撮影

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6. Person to be contacted in applicant's home country, in case of emergency :

緊急の際の母国の連絡先

上欄に書ききれない場合には、別紙に記入して添付すること。

X In case that the blank spaces above are not sufficient for information required, please accompany this form with an attached sheet.

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| Applicant's Signature: | |
| 申請者署名 | |
| Applicant's Name (in Roman block capitals): 申請者氏名 | |
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LETTER OF RECOMMENDATION

推薦状

To the President of TOYOTA TECHNOLOGICAL INSTITUTE 豊田工業大学長 殿 Recommendee 被推薦者 Name 氏名:_____ Date of Birth 生年月日: Nationality 国籍: I hereby recommend the person above as a qualified applicant for the double degree course of Toyota **Technological Institute.** 上記の者をダブルディグリープログラム派遣学生として推薦します。 Date : _____ 目付 month day year Recommender 推薦者 (The recommender must be the department chair of the home university. 推薦者は学科(専攻)長とする) Signature: 署名

Name in print:

Title and Institution:

役 職

氏 名